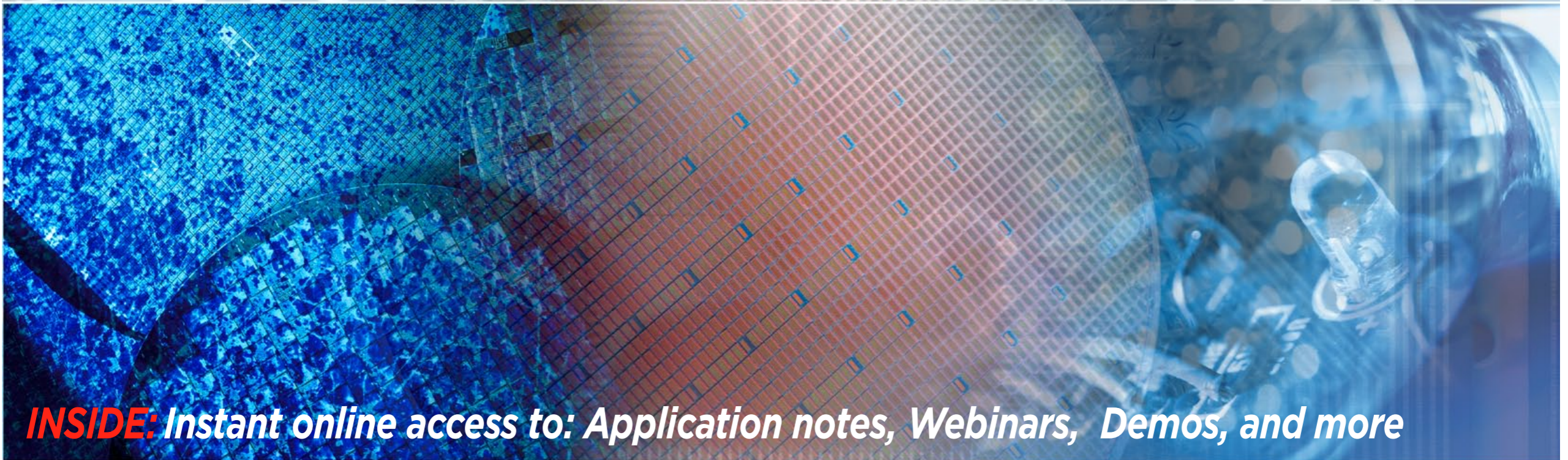


Looking for semi characterization solutions for applications from R&D to high throughput production?

# Learn how to solve today's material and device characterization challenges.



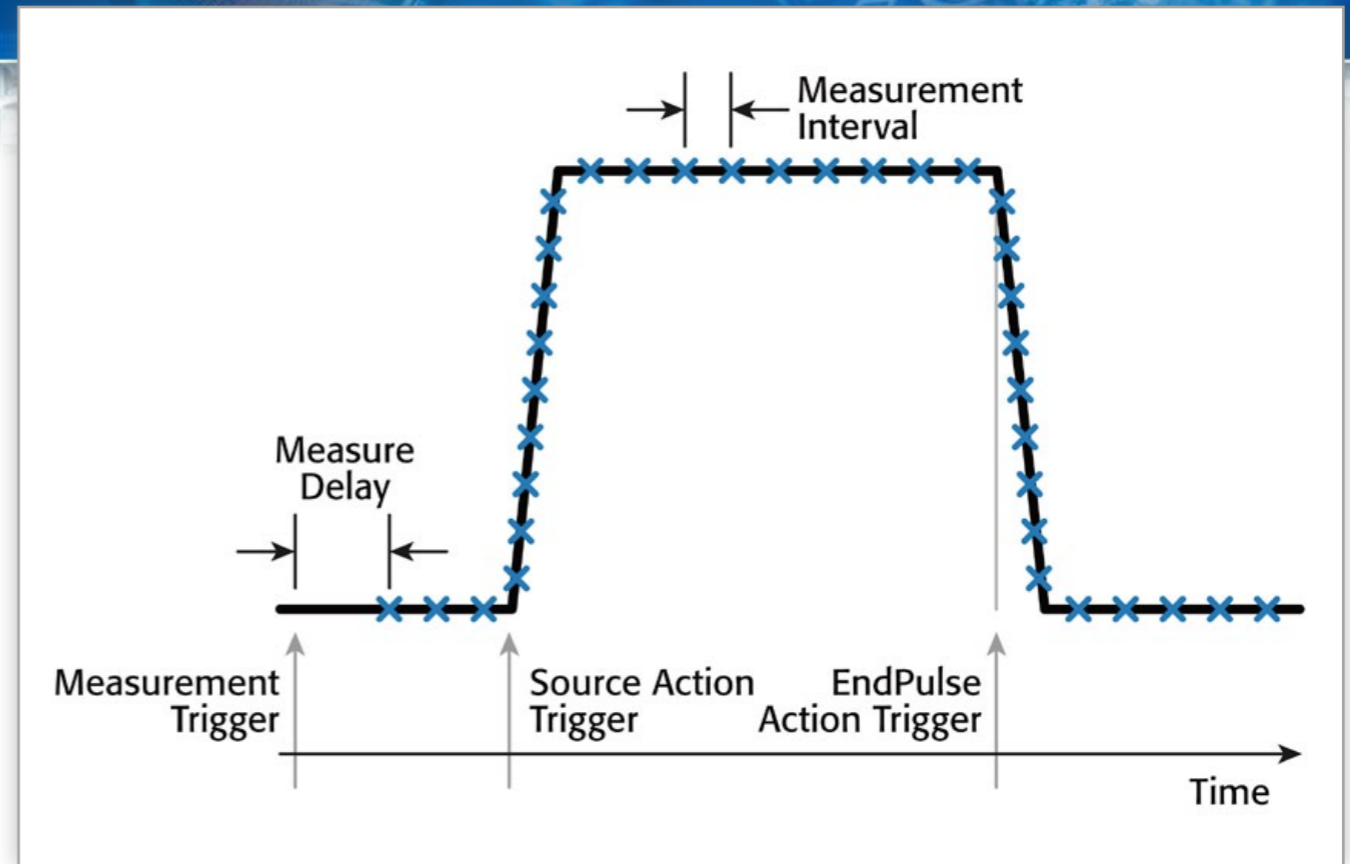
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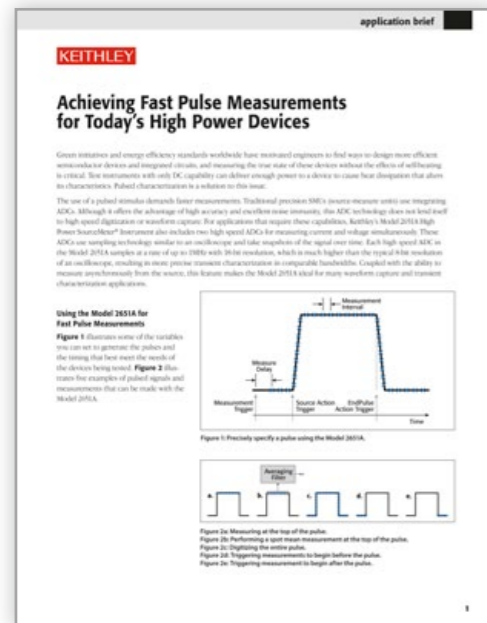
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# Make Fast Pulse Measurements on High Power Devices.

Green initiatives and energy efficiency standards worldwide have motivated engineers to find ways to design more efficient semiconductor devices and integrated circuits; measuring the characteristics of these devices without self-heating effects is critical. DC test instruments often stimulate a device with voltage or current that causes excessive heat dissipation. Pulsed stimulation is a solution, but the pulses and measurement instruments must be fast enough to provide accurate results, particularly when characterizing transient behavior. [Learn more.](#)



Variables that can be set to generate the pulses and timing that best meet the needs of the devices being tested.



## Want to learn more?

Learn how to achieve the fast, pulsed measurements needed for today's high power devices.

[Download our free online application brief.](#)

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[Send us your question](#) or [join the discussion on our application forum.](#)



## View our online demo.

Learn how two Model 2651A High Power SourceMeter instruments can be combined for 100A pulses.

# Discover the Model 2651A, where high power meets high performance test and measurement.



Our new **Model 2651A High Power System SourceMeter® Instrument** simplifies characterizing today's challenging high power electronics with unprecedented power, precision, speed, flexibility, and ease of use. It combines a highly flexible, four-quadrant voltage and current source/load with precision voltage and current meters.

- Source or sink 2,000W of pulsed power ( $\pm 40V$ ,  $\pm 50A$ ), 200W of DC power ( $\pm 10V@ \pm 20A$ ,  $\pm 20V@ \pm 10A$ ,  $\pm 40V@ \pm 5A$ )
- Easily connect two units (in series or parallel) to create solutions up to  $\pm 100A$  or  $\pm 80V$
- 1pA resolution enables precise measurement of very low leakage currents
- $1\mu s$  per point (1MHz), 18-bit sampling, accurately characterizes transient behavior

With the Model 2651A, you can choose from either digitizing or integrating measurement modes. The digitizing measurement mode enables the capture of transient behavior such as changing thermal effects with  $1\mu s$  per point (1MHz) sampling. The integrating measurement mode enables extremely accurate and repeatable measurements.



**Need more detail?**  
[Download the Model 2651A datasheet.](#)

A single Model 2651A unit can source and sink up to  $\pm 40V$  and  $\pm 50A$ . Learn how two of these instruments can be combined to test to 100A for the testing of devices that operate at currents beyond that of a single Model 2651A instrument. [Download our application brief.](#)

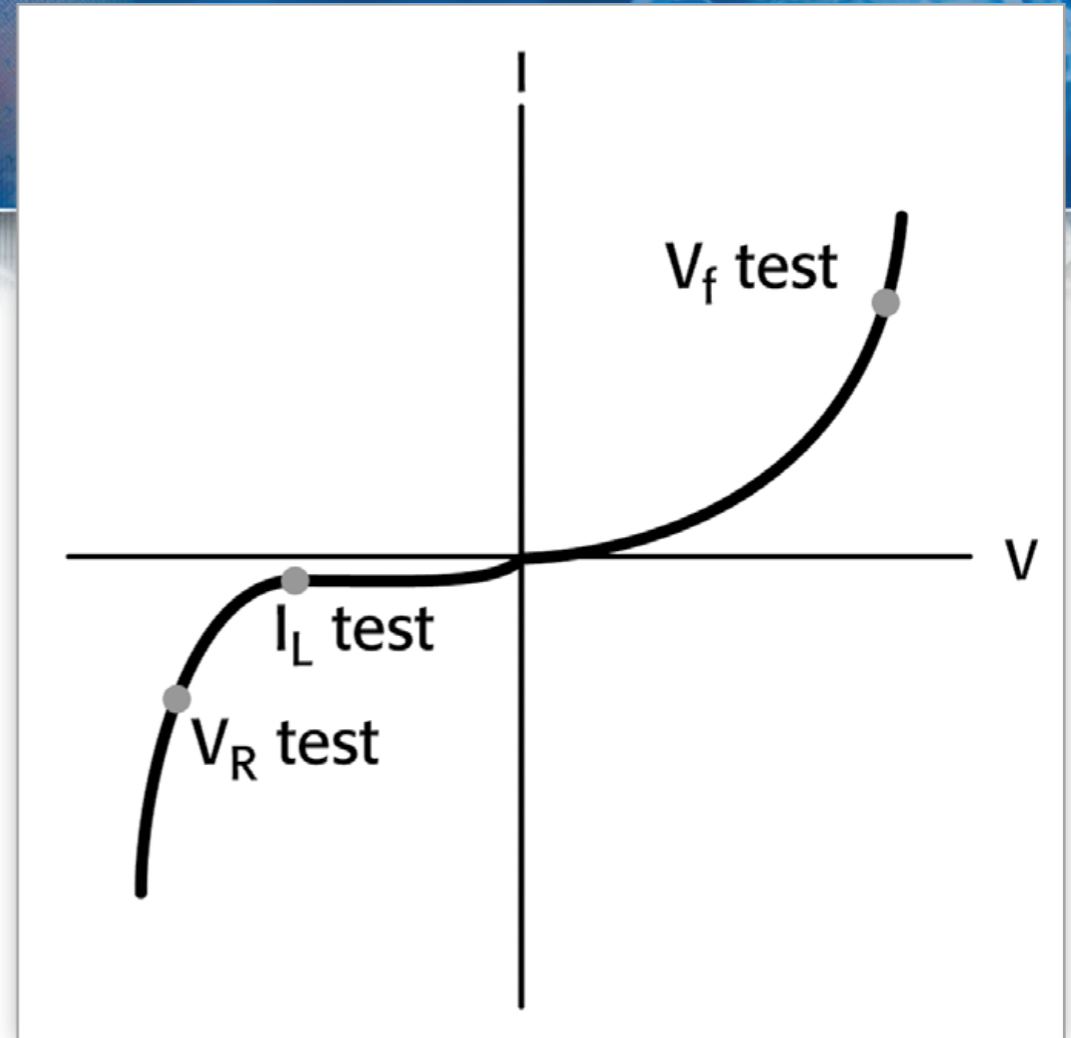
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# Test high brightness LEDs faster and more confidently.

The high efficiency and long lifetimes of visible light emitting diodes (LEDs) make them invaluable for a growing range of applications. Extensive R&D has led to the creation of High Brightness LEDs with higher luminous flux, longer lifetimes, greater chromaticity, and more lumens per watt. Testing HBLEDs typically involves both optical and electrical characterization, including verifying forward operating voltage ( $V_F$ ), optical power measurements, reverse breakdown voltage ( $V_R$ ) and leakage current ( $I_L$ ) tests. [Learn more.](#)



Typical LED DC I-V curve and test points (not to scale)

## Want to learn more?

Learn how to achieve higher LED test throughput and reduce the cost of test using new technologies, including instruments enabled with Keithley's Test Script Processor (TSP®).

[Read our online application note.](#)



Let us offer advice on your application.

[Send us your question or join the discussion on our application forum.](#)



Watch our HBLED testing online webinar.

# Get the tools you need for HLED testing with Series 2600A System SourceMeter® instruments.



**Series 2600A System SourceMeter instruments** are our latest I-V source-measure instruments for use as either bench-top I-V characterization tools or as building block components of multi-channel I-V test systems. Bench-top instrument users can quickly and easily perform common I-V tests without programming or installing software. For system-level applications, Series 2600A's **Test Script Processor (TSP®)** architecture, along with other new capabilities such as parallel test execution and precision timing, provides the highest throughput in the industry, lowering the cost of test.

- Combines a power supply, true current source, DMM, arbitrary waveform generator, V or I pulse generator with measurement, electronic load, and trigger controller – all in one instrument
- Family of products offers wide dynamic range: 1fA to 10A and 1μV to 200V
- 20,000 rdgs/s provides faster test times and ability to capture transient device behavior
- Precision timing and channel synchronization (<500ns)

Series 2600A instruments offer the unique ability to increase the throughput of complicated test sequences for LEDs and other devices dramatically by having dedicated test script processors running in parallel on each instrument.

**Need more detail?**  
**Download the Series 2600A datasheet.**



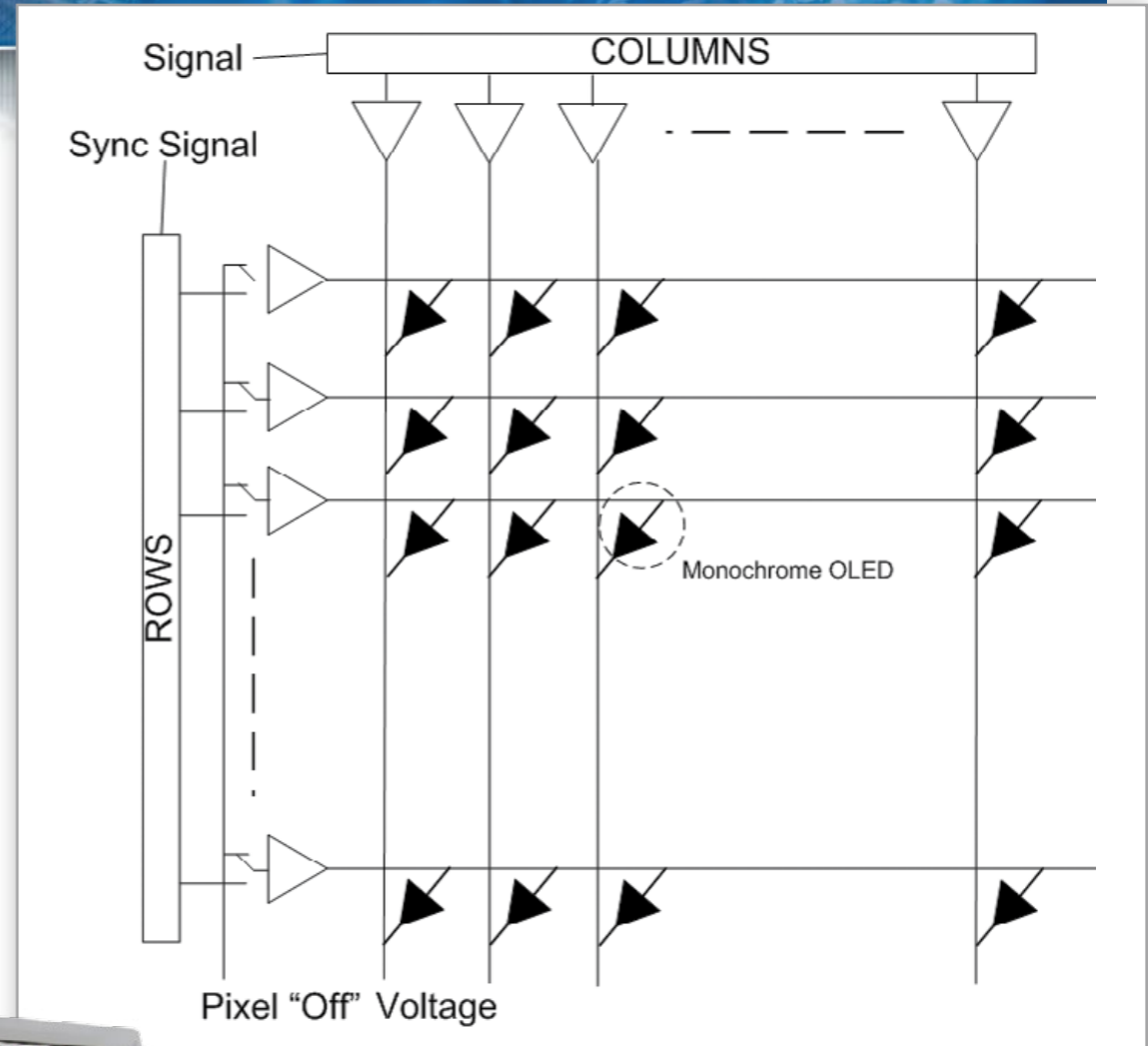
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# Test passive matrix OLED displays accurately and cost-effectively.

During R&D and production, characterizing an Organic Light Emitting Diode (OLED) display may include testing its I-V performance, reverse bias leakage current, and open/short testing of individual display pixels. An OLED's I-V characteristic roughly approximates a diode. However, it also has different characteristics due to the disordered nature of the materials and much lower carrier mobilities than highly ordered semiconductors. The resulting formation of space charges produces numerous transient effects. Current hysteresis resulting from the direction and speed of the sweep voltage is also present. These effects must be properly characterized and understood before DC test results can be correlated with the quality of the display. [Learn more.](#)



A passive matrix OLED (PMOLED) display schematic

**KEITHLEY** Number 2002  
Application Note Series  
**DC Production Testing of OLED Displays**

**Introduction**  
Organic Light Emitting Diode (OLED) displays employ an emerging flat panel technology. Layers of certain organic materials form a p-n junction that emits light when injected carriers recombine. In an OLED display, individual OLEDs form pixels, which are combined in a row and column matrix configuration. An OLED may be monochrome (black or white) or a stacked OLED, which generates more than one color. A typical color OLED display is made up of RGB (red, green, blue) pixels. Displays may employ either active or passive addressing schemes (both not both) to illuminate the pixels. Passive addressing, illustrated in Figure 2, is both less complex and less costly than active addressing and is the most common method used in small displays.

**Test Descriptions**  
Several electrical specifications are important to the performance of OLEDs and OLED displays:  
• Reverse bias leakage current  
• Sweep forward and reverse bias I-V characteristics  
• Short and open testing of display pixels

Each of these tests will first be discussed in the context of measuring an individual pixel. By using electrical switching, the tests can then be scaled up for multi-pixel displays of various sizes.

**Reverse Bias Leakage Current**  
The choice of test equipment, cabling, and fixtures for reverse bias leakage measurements is dictated by the magnitude of the leakage current and the desired measurement accuracy. The leakage current is simply the current through the device at a specified reverse bias voltage. As such, the test system must be able to source a stable voltage across the device and measure the relatively small current flow accurately. For some products, a leakage current that's less than a predetermined threshold, (e.g., several bits of leakage) may serve as a substitute for an acceptable product. In this case, a simple go/no-go test with a Model 2400 SourceMeter instrument, which provides current measurement accuracy of  $30^{-10}$  to  $10^{-14}$  A, is adequate. It's possible to measure currents as low as  $10^{-14}$  A if an electrometer with a voltage source, a properly guarded fixture, and trace cabling are used.

**Forward and Reverse Bias I-V Characteristics**  
The configuration described in the "Reverse Bias Leakage Current" section can also be used to make forward and reverse bias voltage sweeps and current measurements. Both the Model 2400 and the Model 6517A contain bipolar voltage sources that are controlled by a microprocessor. This makes it possible to source a series of voltages, measure the corresponding current, and store the measurements in memory until the sweep is

**Figure 1:** Schematic representation of a passive matrix OLED (PMOLED) display.

**Figure 2:** A connection schematic that illustrates performing a reverse bias leakage measurement on a single OLED.

Learn how to test OLED displays faster and more accurately. [Download our free online application note.](#)



[View our online demo.](#)

Let us offer advice on your application.  
[Send us your question or join the discussion on our application forum.](#)

# Characterize the I-V performance of OLED displays faster with Series 2400 SourceMeter instruments.



**Series 2400 SourceMeter instruments** are designed specifically for testing devices like OLED displays, which demand tightly coupled precision voltage and current sourcing as well as measurement capabilities. Each is both a highly stable DC power source and a true instrument-grade 5½-digit multimeter. The power source characteristics include low noise, precision, and readback. The multimeter capabilities include high repeatability and low noise. The result is a compact, single-channel, DC parametric tester.

- Six models: 20–100W DC, 1000W pulsed, 1100V to 1μV, 10A to 10pA
- Source and sink (4-quadrant) operation
- 0.012% basic measure accuracy with 5½-digit resolution
- Optional high speed sense lead contact check function
- Programmable DIO port for automation/handler/prober control



This OLED characterization system is configured with a Model 7002 Switch Mainframe, Model 2361 Trigger Controller, and four Model 2400 SourceMeter instruments.

**Need more details about Series 2400 SourceMeter instruments?**  
**Download our white paper, *New Test Realities for Evolving FPD Technologies.***



**Want assistance, a quote, or to place an order?**

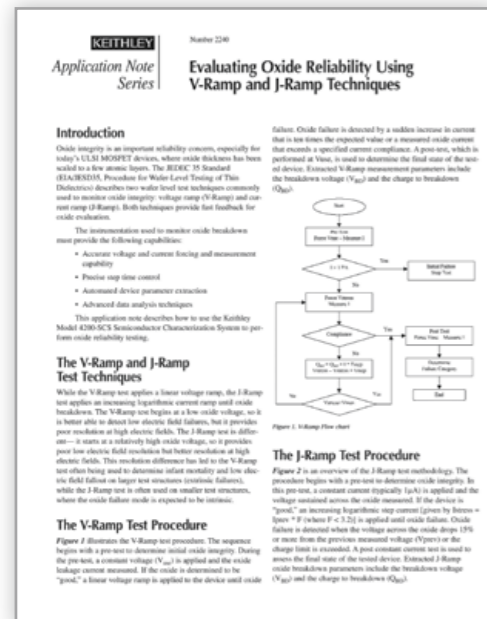
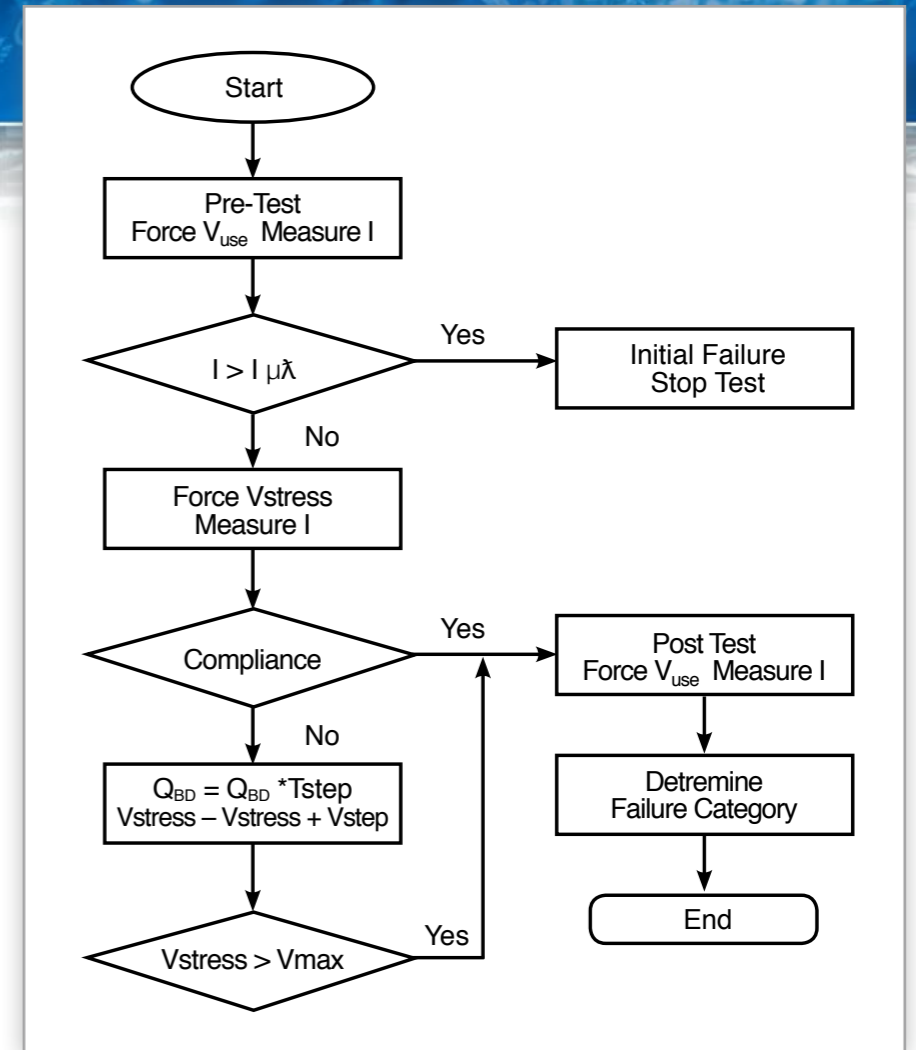
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# Monitor oxide breakdown with confidence.

Oxide integrity is an important reliability concern, especially for modern ULSI MOSFET devices, where oxide thickness has been scaled to a few atomic layers. The JEDEC 35 Standard (EIA/JESD35, Procedure for Wafer-Level Testing of Thin Dielectrics) describes two wafer level test techniques commonly used to monitor oxide integrity: voltage ramp (V-Ramp) and current ramp (J-Ramp). Both techniques provide fast feedback for oxide evaluation. [Learn more.](#)

A V-Ramp test procedure begins with a pre-test to determine initial oxide integrity. During the pre-test, a constant voltage ( $V_{use}$ ) is applied and the oxide leakage current measured. If the oxide is determined to be “good,” a linear voltage ramp is applied to the device until oxide failure. Oxide failure is detected by a sudden increase in current that is ten times the expected value or a measured oxide current that exceeds a specified current compliance. A post-test, performed at  $V_{use}$ , is used to determine the final state of the tested device. Extracted V-Ramp measurement parameters include the breakdown voltage ( $V_{BD}$ ) and the charge to breakdown ( $Q_{BD}$ ).



Want to learn more?  
[Download our free online application note.](#)



Keithley's Model 4200-SCS Semiconductor Characterization System offers a cost-effective solution for oxide reliability testing. [Learn more about the Model 4200-SCS.](#)

Let us offer advice on your application.  
[Send us your question](#) or [join the discussion on our application forum.](#)



# Get the accurate oxide integrity data you need easily with the Model 4200-SCS Semiconductor Characterization System.

Monitoring oxide breakdown demands instrumentation capable of providing accurate voltage and current forcing and measurement, precise step time control, automated device parameter extraction, and advanced data analysis techniques. The **Model 4200-SCS's** built-in test sequencer and Interactive Test Module (ITM) capability simplify implementing both V-Ramp and J-Ramp test algorithms, as illustrated in V-Ramp test sequence shown below. The Project Navigator window displays the test sequence, which begins with a pre-test, followed by a linear voltage ramp to oxide breakdown. A post-test determines the final device state.



V-Ramp project test sequence and test definition.

Need more details about the Model 4200-SCS Semiconductor Characterization System? [Download the datasheet.](#)



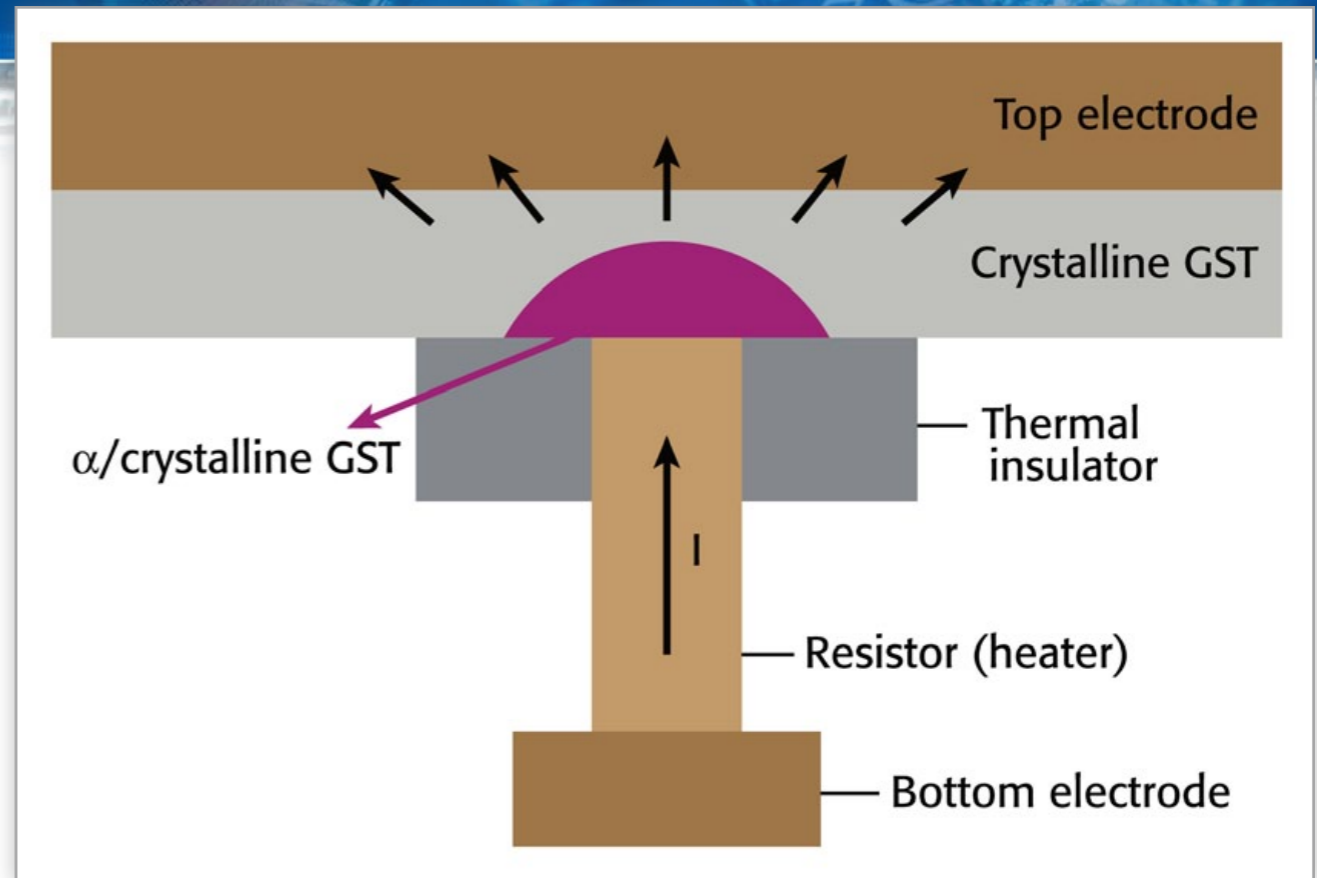
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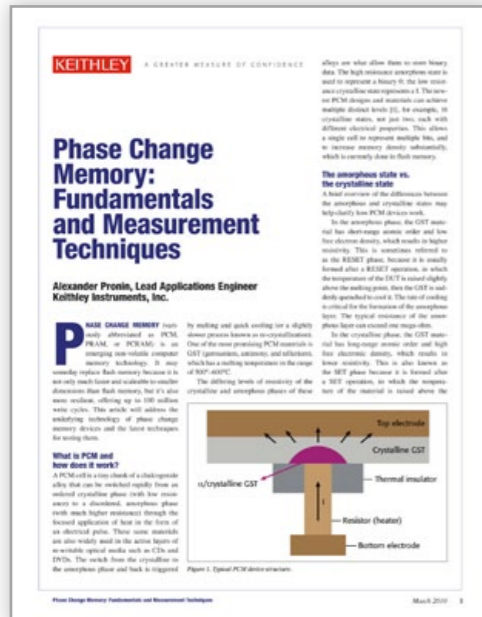
# Characterize highly advanced phase change memory devices.

A phase change memory (PCM) cell is a tiny chunk of a chalcogenide alloy that can be switched rapidly from an ordered crystalline phase (with low resistance) to a disordered, amorphous phase (with much higher resistance) through the focused application of heat in the form of an electrical pulse. The differing levels of resistivity of the crystalline and amorphous phases are what allow them to store binary data. The ability to develop new PCM materials and refine device designs will depend largely on manufacturers' ability to characterize several parameters accurately, including recrystallization rate, data retention, cycling endurance, drift of the cell's resistance over time, impact of the "read" procedure on the stored state, and resistance-current (RI) and I-V curves. [Learn more.](#)



GST (germanium, antimony, and tellurium) is one of the most promising PCM materials: in its amorphous phase, its typical resistance can exceed 1MΩ; in the crystalline phase, it ranges from 1 to 10kΩ.

Want to learn more?  
Download our free online article.



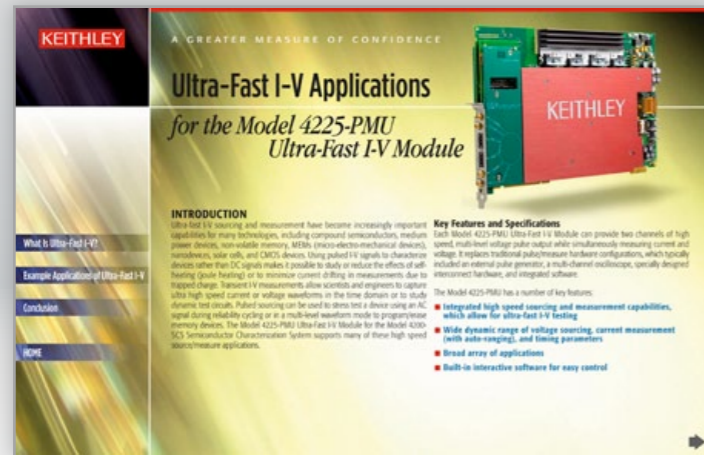
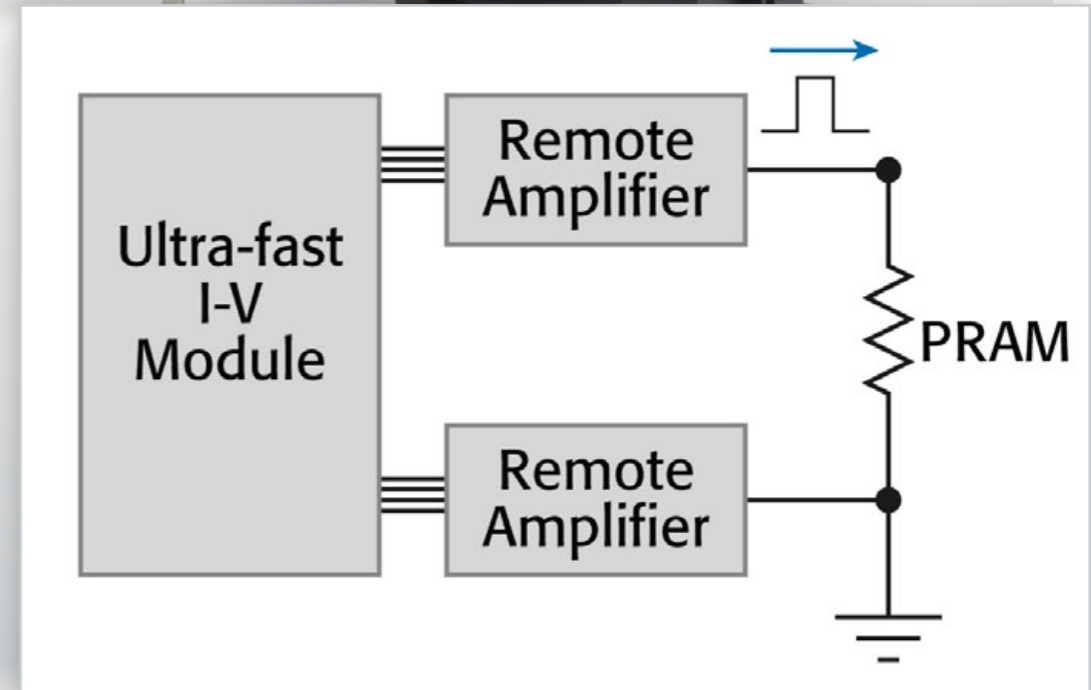
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# Shorten PCM test times with the Model 4225-PMU Ultra-Fast I-V Module.

The **Model 4225-PMU Ultra-Fast I-V Module** offers the ideal solution for testing single memory cells or a small array of cells, such as when isolated cells need to be tested in research and development or for process verification. Because the 4225-PMU can be used for both the pulsing and measurement, total test time is reduced. The **Model 4225-PMU** and the **Model 4225-RPM Remote Amplifier/Switches** that extend its sensitivity are designed to integrate with the Model 4200-SCS Semiconductor Characterization System, which not only provides a wide range of other measurement functions necessary to characterize a PCM device but offers the ability to automate the entire testing process.

The dynamic switch from a high- to a low-resistive state in the presence of a load resistor produces a characteristic RI curve with a snapback, an area of negative resistance. Snapback itself is not a feature of PCMs or of PCM testing but rather a side effect of the R-load technique long used to obtain both RI and I-V curves. The Model 4225-PMU eliminates the need for the load resistor, as well as the snapback side effect problem, and provides tight control over the level of current sourced for more accurate characterization of low currents in the RI curve. The Model 4225-PMU can source voltage and simultaneously measure both voltage and current responses with high accuracy, with rise and fall times as short as 20ns.



**Want to learn more about the Model 4225-PMU?**  
**To learn more about ultra-fast I-V sourcing and measurement techniques,**  
**download our Ultra-Fast I-V applications e-book.**

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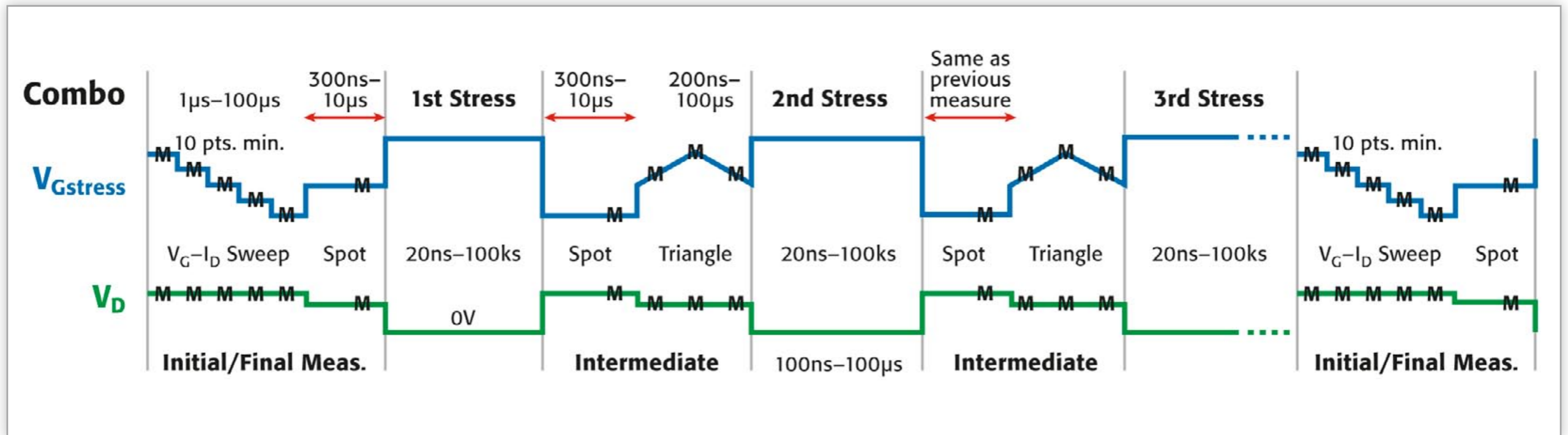
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# Model and monitor Bias Temperature Instability (BTI) for CMOS transistors.

Modeling negative bias temperature instability (NBTI) is a challenge when developing deeply scaled silicon CMOS transistor designs. Over time, NBTI effects cause a transistor's threshold voltage ( $V_T$ ) to shift and its sub-threshold drain current to increase significantly, severely limiting transistor lifetime and circuit performance. These effects must be accurately modeled during device development and monitored during process integration and production. During

BTI characterization, the transistor is alternately stressed and characterized. However, the BTI mechanism is susceptible to relaxation effects, which means that the instant the stress is removed, the transistor starts to recover and the degradation fades. Characterizing the degradation prior to relaxation demands the use of ultra-fast I-V techniques. [Learn more.](#)



A typical stress/measure waveform that can be used to characterize BTI.

Let us offer advice on your application.

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# Discover everything you need for NBTI and PBTI measurements in the Model 4200-BTI-A Ultra-Fast BTI Package.

The **Model 4200-BTI-A Ultra-Fast BTI Package** is the industry's most advanced NBTI/PBTI test platform, with everything needed to make sophisticated NBTI and PBTI measurements on leading-edge silicon CMOS technology: a Model 4225-PMU Ultra-Fast I-V Module, two Model 4225-RPM Remote Amplifier/Switches, Automated Characterization Suite (ACS) software, an Ultra-Fast BTI Test Project Module, and cabling. The test software module makes it easy to define stress timing, stress conditions, and a wide range of measurement sequences from spot  $I_D$ , On-The-Fly (OTF), or  $I_D$ - $V_G$  sweeps. It allows measuring recovery effects as well as degradation and offers prestress and poststress measurement options that incorporate the Model 4200-SCS's DC SMUs for precision low-level measurements.



The Ultra-Fast BTI test software module supports spot, step sweep, smooth sweep, and sample measurement types. Each type's timing is defined by the test sample rate and the individual measurement settings. The software module also provides control over the voltage conditions between each element in the test sequence, for maximum flexibility and ease of use, even when defining complex test sequences.

**Want to learn more about the Model 4200-BTI-A Package?**

Discover ultra-fast I-V sourcing and measurement techniques being used for NBTI/PBTI measurements by [downloading our Ultra-Fast I-V applications e-book.](#)

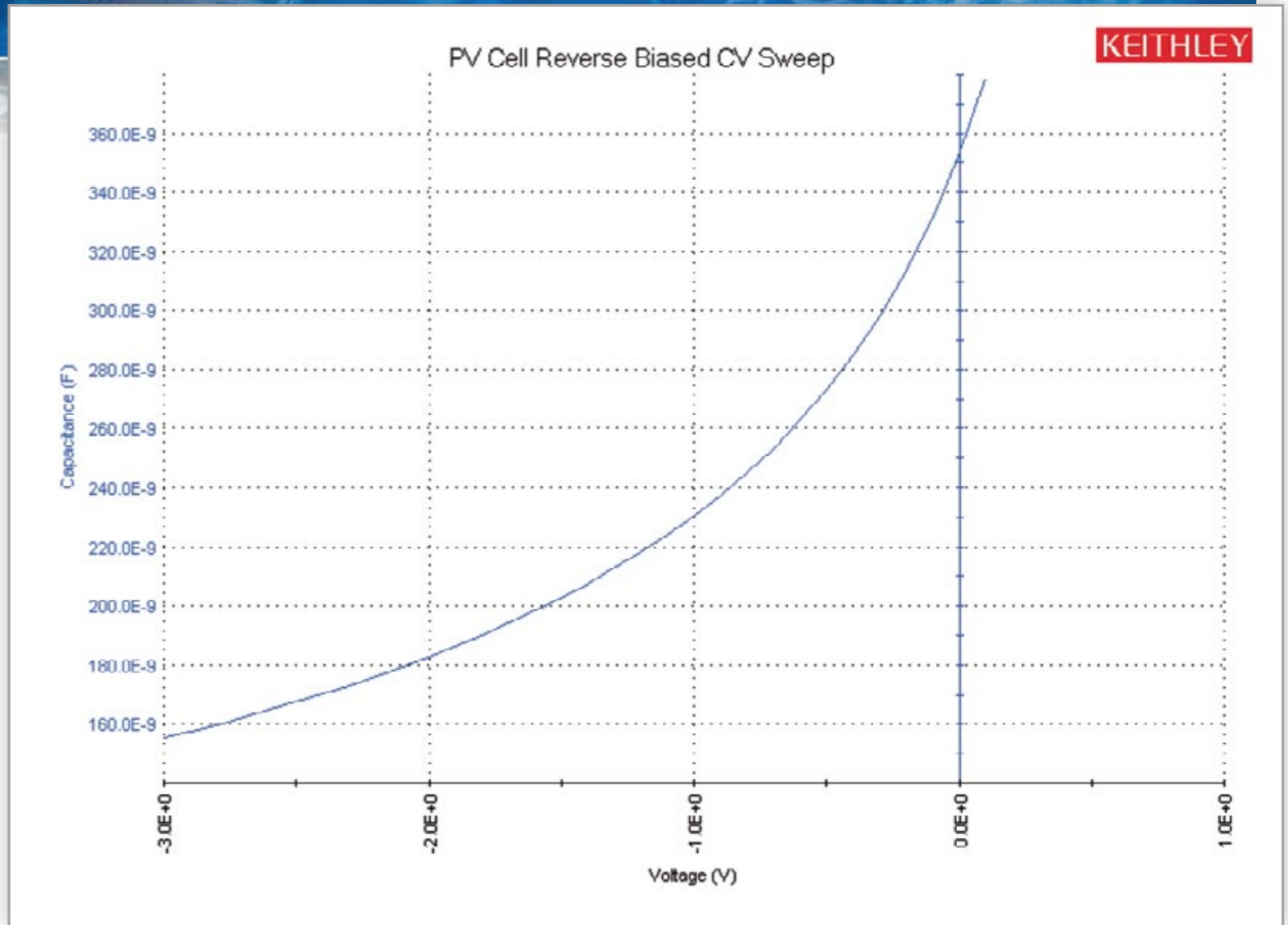
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# Characterize solar cells with C-V measurements.

Capacitance-voltage (C-V) measurements are useful in deriving particular parameters about solar cells (also known as photovoltaic or PV devices). Depending on the type of solar cell or photovoltaic material being characterized, C-V measurements can be used to derive parameters such as the doping concentration and the built-in voltage of the junction. A capacitance-frequency (C-f) sweep can be used to provide information on the existence of traps in the depletion region. Some tests require pulsed current-voltage (I-V) measurements. These measurements are usually performed at different light intensities and under different temperature conditions. [Learn more.](#)



A C-V sweep of a silicon solar cell

**KEITHLEY** Number 5025  
Application Note Series

### Electrical Characterization of Photovoltaic Materials and Solar Cells with the Model 4200-SCS Semiconductor Characterization System

I-V, C-V, C-f, DLCP, Pulsed I-V, Resistivity, and Hall Voltage Measurements

**Introduction**  
The increasing demand for clean energy and the largely untapped potential of the sun as an energy source is making solar energy conversion technology increasingly important. As a result, the demand for solar cells, which convert sunlight directly into electricity, is growing. Solar or photovoltaic (PV) cells are made up of semiconductor materials that absorb photons from sunlight and then release electrons, causing an electric current to flow when the cell is connected to a load. A variety of measurements are used to characterize a solar cell's performance, including its output and its efficiency. This electrical characterization is performed as part of research and development of photovoltaic cells and materials, as well as during the manufacturing process.

**Making Electrical Measurements with the Model 4200-SCS**  
To simplify testing photovoltaic materials and cells, the Model 4200-SCS is supported with a test program for making many of the readily commonly used measurements easily. These tests, which include I-V, capacitance, and resistance measurements, also include formulas for extracting common parameters such as the maximum power, short circuit current, diode ideality, etc. The SolarCell project (Figure 2) is included with all Model 4200-SCS systems running KTEL Version 6.0 or later. It provides characterization (Table 1) in the form of ITCM characterizer, Test Module, and UTM (User Test Module) for electrical characterization.

Parameter	Test Module	Description
I-V	DLCP	Perform I-V sweep and calculate $I_{sc}$ , $V_{oc}$ , $I_{mp}$ , $V_{mp}$ , $P_{mp}$ , $R_{sh}$ , $R_{s}$ , $n$ , $I_0$ , $I_{01}$ , $I_{02}$ , $I_{03}$ , $I_{04}$ , $I_{05}$ , $I_{06}$ , $I_{07}$ , $I_{08}$ , $I_{09}$ , $I_{10}$ , $I_{11}$ , $I_{12}$ , $I_{13}$ , $I_{14}$ , $I_{15}$ , $I_{16}$ , $I_{17}$ , $I_{18}$ , $I_{19}$ , $I_{20}$ , $I_{21}$ , $I_{22}$ , $I_{23}$ , $I_{24}$ , $I_{25}$ , $I_{26}$ , $I_{27}$ , $I_{28}$ , $I_{29}$ , $I_{30}$ , $I_{31}$ , $I_{32}$ , $I_{33}$ , $I_{34}$ , $I_{35}$ , $I_{36}$ , $I_{37}$ , $I_{38}$ , $I_{39}$ , $I_{40}$ , $I_{41}$ , $I_{42}$ , $I_{43}$ , $I_{44}$ , $I_{45}$ , $I_{46}$ , $I_{47}$ , $I_{48}$ , $I_{49}$ , $I_{50}$ , $I_{51}$ , $I_{52}$ , $I_{53}$ , $I_{54}$ , $I_{55}$ , $I_{56}$ , $I_{57}$ , $I_{58}$ , $I_{59}$ , $I_{60}$ , $I_{61}$ , $I_{62}$ , $I_{63}$ , $I_{64}$ , $I_{65}$ , $I_{66}$ , $I_{67}$ , $I_{68}$ , $I_{69}$ , $I_{70}$ , $I_{71}$ , $I_{72}$ , $I_{73}$ , $I_{74}$ , $I_{75}$ , $I_{76}$ , $I_{77}$ , $I_{78}$ , $I_{79}$ , $I_{80}$ , $I_{81}$ , $I_{82}$ , $I_{83}$ , $I_{84}$ , $I_{85}$ , $I_{86}$ , $I_{87}$ , $I_{88}$ , $I_{89}$ , $I_{90}$ , $I_{91}$ , $I_{92}$ , $I_{93}$ , $I_{94}$ , $I_{95}$ , $I_{96}$ , $I_{97}$ , $I_{98}$ , $I_{99}$ , $I_{100}$
C-V	DLCP	Perform C-V sweep and calculate $C_{j0}$ , $C_{j1}$ , $C_{j2}$ , $C_{j3}$ , $C_{j4}$ , $C_{j5}$ , $C_{j6}$ , $C_{j7}$ , $C_{j8}$ , $C_{j9}$ , $C_{j10}$ , $C_{j11}$ , $C_{j12}$ , $C_{j13}$ , $C_{j14}$ , $C_{j15}$ , $C_{j16}$ , $C_{j17}$ , $C_{j18}$ , $C_{j19}$ , $C_{j20}$ , $C_{j21}$ , $C_{j22}$ , $C_{j23}$ , $C_{j24}$ , $C_{j25}$ , $C_{j26}$ , $C_{j27}$ , $C_{j28}$ , $C_{j29}$ , $C_{j30}$ , $C_{j31}$ , $C_{j32}$ , $C_{j33}$ , $C_{j34}$ , $C_{j35}$ , $C_{j36}$ , $C_{j37}$ , $C_{j38}$ , $C_{j39}$ , $C_{j40}$ , $C_{j41}$ , $C_{j42}$ , $C_{j43}$ , $C_{j44}$ , $C_{j45}$ , $C_{j46}$ , $C_{j47}$ , $C_{j48}$ , $C_{j49}$ , $C_{j50}$ , $C_{j51}$ , $C_{j52}$ , $C_{j53}$ , $C_{j54}$ , $C_{j55}$ , $C_{j56}$ , $C_{j57}$ , $C_{j58}$ , $C_{j59}$ , $C_{j60}$ , $C_{j61}$ , $C_{j62}$ , $C_{j63}$ , $C_{j64}$ , $C_{j65}$ , $C_{j66}$ , $C_{j67}$ , $C_{j68}$ , $C_{j69}$ , $C_{j70}$ , $C_{j71}$ , $C_{j72}$ , $C_{j73}$ , $C_{j74}$ , $C_{j75}$ , $C_{j76}$ , $C_{j77}$ , $C_{j78}$ , $C_{j79}$ , $C_{j80}$ , $C_{j81}$ , $C_{j82}$ , $C_{j83}$ , $C_{j84}$ , $C_{j85}$ , $C_{j86}$ , $C_{j87}$ , $C_{j88}$ , $C_{j89}$ , $C_{j90}$ , $C_{j91}$ , $C_{j92}$ , $C_{j93}$ , $C_{j94}$ , $C_{j95}$ , $C_{j96}$ , $C_{j97}$ , $C_{j98}$ , $C_{j99}$ , $C_{j100}$
C-f	DLCP	Perform C-f sweep and calculate $f_{t0}$ , $f_{t1}$ , $f_{t2}$ , $f_{t3}$ , $f_{t4}$ , $f_{t5}$ , $f_{t6}$ , $f_{t7}$ , $f_{t8}$ , $f_{t9}$ , $f_{t10}$ , $f_{t11}$ , $f_{t12}$ , $f_{t13}$ , $f_{t14}$ , $f_{t15}$ , $f_{t16}$ , $f_{t17}$ , $f_{t18}$ , $f_{t19}$ , $f_{t20}$ , $f_{t21}$ , $f_{t22}$ , $f_{t23}$ , $f_{t24}$ , $f_{t25}$ , $f_{t26}$ , $f_{t27}$ , $f_{t28}$ , $f_{t29}$ , $f_{t30}$ , $f_{t31}$ , $f_{t32}$ , $f_{t33}$ , $f_{t34}$ , $f_{t35}$ , $f_{t36}$ , $f_{t37}$ , $f_{t38}$ , $f_{t39}$ , $f_{t40}$ , $f_{t41}$ , $f_{t42}$ , $f_{t43}$ , $f_{t44}$ , $f_{t45}$ , $f_{t46}$ , $f_{t47}$ , $f_{t48}$ , $f_{t49}$ , $f_{t50}$ , $f_{t51}$ , $f_{t52}$ , $f_{t53}$ , $f_{t54}$ , $f_{t55}$ , $f_{t56}$ , $f_{t57}$ , $f_{t58}$ , $f_{t59}$ , $f_{t60}$ , $f_{t61}$ , $f_{t62}$ , $f_{t63}$ , $f_{t64}$ , $f_{t65}$ , $f_{t66}$ , $f_{t67}$ , $f_{t68}$ , $f_{t69}$ , $f_{t70}$ , $f_{t71}$ , $f_{t72}$ , $f_{t73}$ , $f_{t74}$ , $f_{t75}$ , $f_{t76}$ , $f_{t77}$ , $f_{t78}$ , $f_{t79}$ , $f_{t80}$ , $f_{t81}$ , $f_{t82}$ , $f_{t83}$ , $f_{t84}$ , $f_{t85}$ , $f_{t86}$ , $f_{t87}$ , $f_{t88}$ , $f_{t89}$ , $f_{t90}$ , $f_{t91}$ , $f_{t92}$ , $f_{t93}$ , $f_{t94}$ , $f_{t95}$ , $f_{t96}$ , $f_{t97}$ , $f_{t98}$ , $f_{t99}$ , $f_{t100}$
DLCP	DLCP	Perform DLCP sweep and calculate $R_{sh}$ , $R_{s}$ , $n$ , $I_0$ , $I_{01}$ , $I_{02}$ , $I_{03}$ , $I_{04}$ , $I_{05}$ , $I_{06}$ , $I_{07}$ , $I_{08}$ , $I_{09}$ , $I_{10}$ , $I_{11}$ , $I_{12}$ , $I_{13}$ , $I_{14}$ , $I_{15}$ , $I_{16}$ , $I_{17}$ , $I_{18}$ , $I_{19}$ , $I_{20}$ , $I_{21}$ , $I_{22}$ , $I_{23}$ , $I_{24}$ , $I_{25}$ , $I_{26}$ , $I_{27}$ , $I_{28}$ , $I_{29}$ , $I_{30}$ , $I_{31}$ , $I_{32}$ , $I_{33}$ , $I_{34}$ , $I_{35}$ , $I_{36}$ , $I_{37}$ , $I_{38}$ , $I_{39}$ , $I_{40}$ , $I_{41}$ , $I_{42}$ , $I_{43}$ , $I_{44}$ , $I_{45}$ , $I_{46}$ , $I_{47}$ , $I_{48}$ , $I_{49}$ , $I_{50}$ , $I_{51}$ , $I_{52}$ , $I_{53}$ , $I_{54}$ , $I_{55}$ , $I_{56}$ , $I_{57}$ , $I_{58}$ , $I_{59}$ , $I_{60}$ , $I_{61}$ , $I_{62}$ , $I_{63}$ , $I_{64}$ , $I_{65}$ , $I_{66}$ , $I_{67}$ , $I_{68}$ , $I_{69}$ , $I_{70}$ , $I_{71}$ , $I_{72}$ , $I_{73}$ , $I_{74}$ , $I_{75}$ , $I_{76}$ , $I_{77}$ , $I_{78}$ , $I_{79}$ , $I_{80}$ , $I_{81}$ , $I_{82}$ , $I_{83}$ , $I_{84}$ , $I_{85}$ , $I_{86}$ , $I_{87}$ , $I_{88}$ , $I_{89}$ , $I_{90}$ , $I_{91}$ , $I_{92}$ , $I_{93}$ , $I_{94}$ , $I_{95}$ , $I_{96}$ , $I_{97}$ , $I_{98}$ , $I_{99}$ , $I_{100}$
UTM	UTM	Perform UTM sweep and calculate $R_{sh}$ , $R_{s}$ , $n$ , $I_0$ , $I_{01}$ , $I_{02}$ , $I_{03}$ , $I_{04}$ , $I_{05}$ , $I_{06}$ , $I_{07}$ , $I_{08}$ , $I_{09}$ , $I_{10}$ , $I_{11}$ , $I_{12}$ , $I_{13}$ , $I_{14}$ , $I_{15}$ , $I_{16}$ , $I_{17}$ , $I_{18}$ , $I_{19}$ , $I_{20}$ , $I_{21}$ , $I_{22}$ , $I_{23}$ , $I_{24}$ , $I_{25}$ , $I_{26}$ , $I_{27}$ , $I_{28}$ , $I_{29}$ , $I_{30}$ , $I_{31}$ , $I_{32}$ , $I_{33}$ , $I_{34}$ , $I_{35}$ , $I_{36}$ , $I_{37}$ , $I_{38}$ , $I_{39}$ , $I_{40}$ , $I_{41}$ , $I_{42}$ , $I_{43}$ , $I_{44}$ , $I_{45}$ , $I_{46}$ , $I_{47}$ , $I_{48}$ , $I_{49}$ , $I_{50}$ , $I_{51}$ , $I_{52}$ , $I_{53}$ , $I_{54}$ , $I_{55}$ , $I_{56}$ , $I_{57}$ , $I_{58}$ , $I_{59}$ , $I_{60}$ , $I_{61}$ , $I_{62}$ , $I_{63}$ , $I_{64}$ , $I_{65}$ , $I_{66}$ , $I_{67}$ , $I_{68}$ , $I_{69}$ , $I_{70}$ , $I_{71}$ , $I_{72}$ , $I_{73}$ , $I_{74}$ , $I_{75}$ , $I_{76}$ , $I_{77}$ , $I_{78}$ , $I_{79}$ , $I_{80}$ , $I_{81}$ , $I_{82}$ , $I_{83}$ , $I_{84}$ , $I_{85}$ , $I_{86}$ , $I_{87}$ , $I_{88}$ , $I_{89}$ , $I_{90}$ , $I_{91}$ , $I_{92}$ , $I_{93}$ , $I_{94}$ , $I_{95}$ , $I_{96}$ , $I_{97}$ , $I_{98}$ , $I_{99}$ , $I_{100}$

**Introduction** (continued)  
Some of the electrical tests commonly performed on solar cells involve measuring current and capacitance as a function of an applied DC voltage. Capacitance measurements are sometimes made as a function of frequency or AC voltage. Some tests require pulsed current-voltage measurements. These measurements are usually performed at different light intensities and under different temperature conditions. A variety of important device parameters can be extracted from the DC and pulsed current-voltage (I-V) and capacitance-voltage (C-V) measurements, including output current, conversion efficiency, maximum power output, doping density, resistivity, etc. Electrical characterization is important in determining how to make the cells as efficient as possible with minimal losses.

**Introduction** (continued)  
Instrumentation such as the Model 4200-SCS Semiconductor Characterization System can simplify testing and analysis when making these critical electrical measurements. The Model 4200-SCS is an integrated system that includes instruments for making DC and ultra low I-V and C-V measurements, as well as control software, graphics, and mathematical analysis capabilities. The Model 4200-SCS is well-suited for performing a wide range of measurements, including DC and pulsed current-voltage (I-V), capacitance-voltage (C-V), capacitance-frequency (C-f), diode level capacitance profiling (DLCP), four-point resistivity ( $\rho_4$ ), and Hall voltage ( $V_H$ ) measurements. This application note describes how to use the Model 4200-SCS to make these electrical measurements on PV cells.

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## Make C-V measurements as easily as I-V with the Model 4210-CVU C-V option.

The **Model 4210-CVU** plugs directly into one of the nine slots in the Model 4200-SCS chassis. It simplifies measuring capacitances from femtofarads (fF) to nanofarads (nF) at frequencies from 1kHz to 10MHz. The system's user-friendly GUI makes it simple to configure linear or custom C-V, C-f, and C-t sweeps with up to 4096 data points. A special project optimized for I-V, C-V, and resistivity testing is provided for characterizing photovoltaic cells of all types, including crystalline, amorphous, and thin film. Diagnostic tools are included to ensure the validity of your C-V test results.

When equipped with a Model 4210-CVU meter, the Model 4200-SCS supports Drive Level Capacitance Profiling (DLCP) testing, a technique for determining the defect density (NDL) as a function of depth of a photovoltaic cell. During the DLCP measurement, the applied AC voltage (peak-to-peak) is swept and the DC voltage is varied while the capacitance is measured. This is in contrast to the conventional C-V profiling technique, in which the  $AC_{rms}$  voltage is fixed and the DC voltage is swept.



**Need more detail?**

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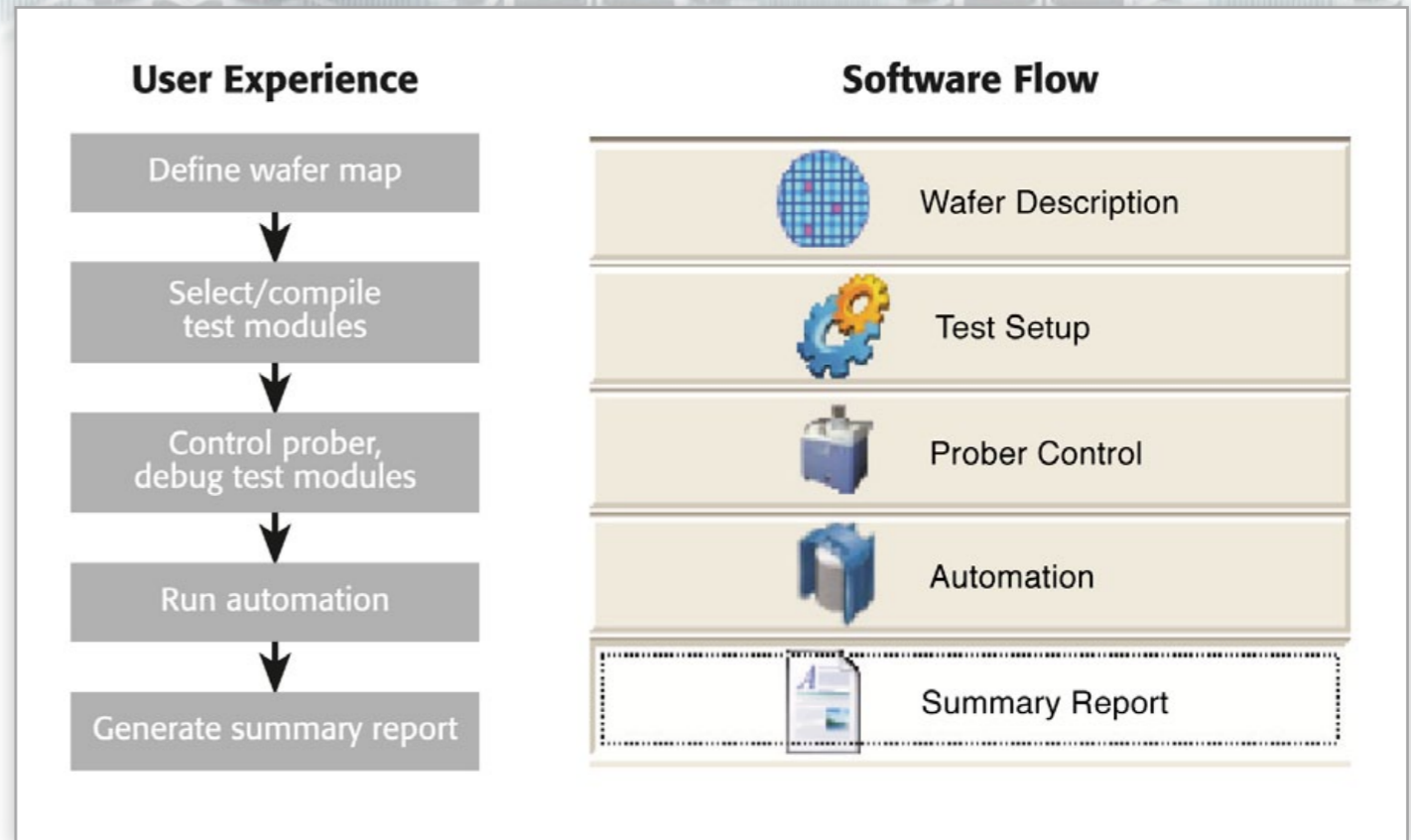
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**Learn more.**



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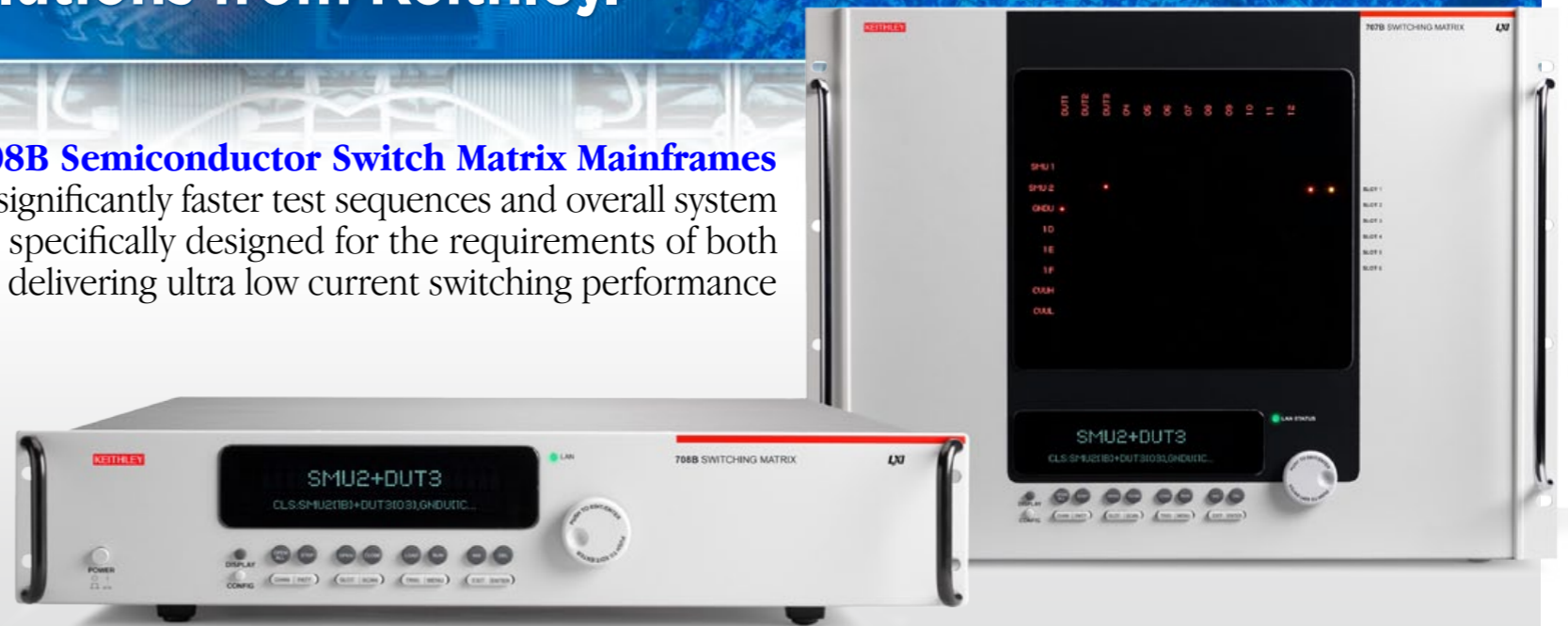
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